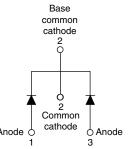


Vishay Semiconductors

Ultrafast Rectifier, 2 x 8 A FRED Pt®





	cathode	
Anode 0	O 2 Commor cathode	

PRODUCT SUMMARY						
Package	TO-220AB					
I _{F(AV)}	2 x 8 A					
V_{R}	200 V					
V _F at I _F	0.895 V					
t _{rr} typ.	See Recovery table					
T _J max.	175 °C					
Diode variation	Common cathode					

FEATURES

- · Ultrafast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- · Designed and qualified according to JEDĔC®-JESD 47
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912



DESCRIPTION / APPLICATIONS

VS-MUR1620CTPbF is the state of the art ultrafast recovery rectifier specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS								
PARAMETER		SYMBOL	TEST CONDITIONS	MAX.	UNITS			
Peak repetitive reverse voltage		V_{RRM}		200	V			
per leg				8.0				
Average rectified forward current to	total device	I _{F(AV)}	Rated V _R , T _C = 150 °C	16	А			
Non-repetitive peak surge current per leg		I _{FSM}		100				
Peak repetitive forward current per leg		I _{FM}	Rated V _R , square wave, 20 kHz, T _C = 150 °C	16				
Operating junction and storage tem	peratures	T _J , T _{Stg}		-65 to +175	°C			

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS				
Breakdown voltage, blocking voltage	V _{BR} , V _R	Ι _R = 100 μΑ	200	-	-			
Forward voltage	V _F	I _F = 8 A		-	0.975	V		
		I _F = 8 A, T _J = 150 °C	-	-	0.895			
B last		V _R = V _R rated	-	-	5			
Reverse leakage current	I _R	T _J = 150 °C, V _R = V _R rated	-	-	250	μΑ		
Junction capacitance	C _T	V _R = 200 V	-	25	-	pF		
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nΗ		



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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
Reverse recovery time		$I_F = 1.0 \text{ A, } dI_F/dt =$	50 A/μs, V _R = 30 V	-	-	35			
		$I_F = 0.5 \text{ A}, I_R = 1.0 \text{ A}, I_{REC} = 0.25 \text{ A}$		-	-	25	no		
	t _{rr}	T _J = 25 °C	I _F = 8 A dI _F /dt = 200 A/μs V _R = 160 V	-	20	-	ns		
		T _J = 125 °C		-	34	-			
Peak recovery current	I _{RRM}	T _J = 25 °C		-	1.7	-	۸		
		T _J = 125 °C		-	4.2	-	A		
Reverse recovery charge	Q _{rr}	T _J = 25 °C		=	23	-	nC		
		T _J = 125 °C		-	75	-	110		

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C		
Thermal resistance, junction to case per leg	R _{thJC}		-	-	3.0			
Thermal resistance, junction to ambient per leg	R _{thJA}		-	-	50	°C/W		
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-			
Waight			-	2.0	-	g		
Weight			-	0.07	-	oz.		
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)		
Marking device		Case style TO-220AB		MUR1	620CT			

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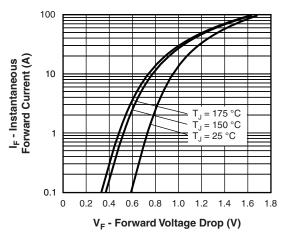


Fig. 1 - Typical Forward Voltage Drop Characteristics

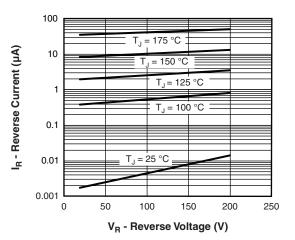


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

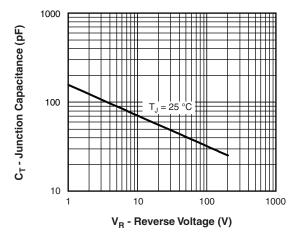


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

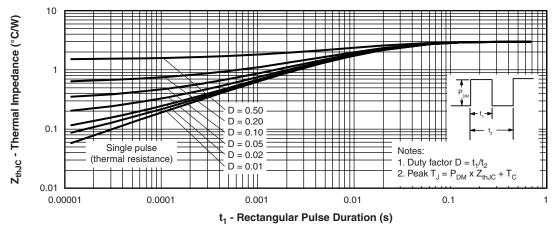


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

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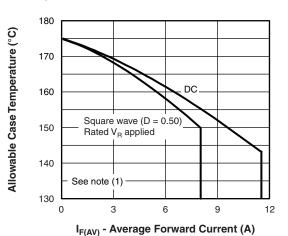


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

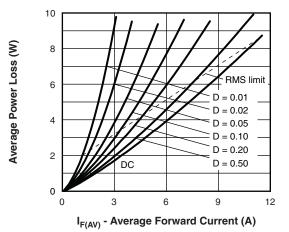


Fig. 6 - Forward Power Loss Characteristics

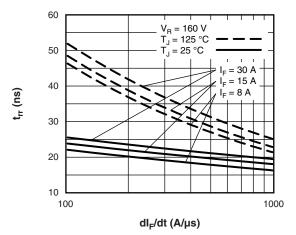


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

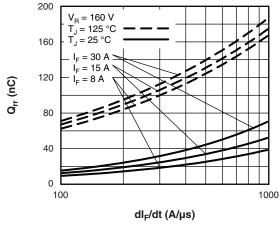


Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

 $\begin{array}{l} \text{(1)} \ \ \text{Formula used:} \ T_C = T_J - (Pd + Pd_{REV}) \times R_{th,JC}; \\ Pd = \text{Forward power loss} = I_{F(AV)} \times V_{FM} \ \text{at } (I_{F(AV)}/D) \ \text{(see fig. 6)}; \\ Pd_{REV} = \text{Inverse power loss} = V_{R1} \times I_R \ \text{(1 - D)}; \ I_R \ \text{at } V_{R1} = \text{Rated } V_R \\ \end{array}$

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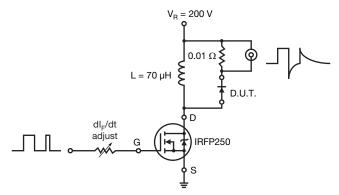
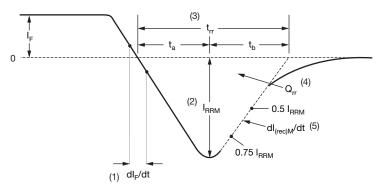


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) $\mathbf{Q}_{\rm rr}$ area under curve defined by $\mathbf{t}_{\rm rr}$ and $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

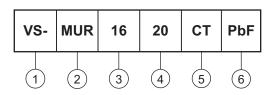
(5) dl_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

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ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Ultrafast MUR series

Current rating (16 = 16 A)

Voltage rating (20 = 200 V)

5 - CT = center tap (dual)

6 - Environmental digit:

PbF = lead (Pb)-free and RoHS-compliant

-N3 = halogen-free, RoHS-compliant and totally lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-MUR1620CTPbF	50	1000	Antistatic plastic tube				
VS-MUR1620CT-N3	50	1000	Antistatic plastic tube				

LINKS TO RELATED DOCUMENTS						
Dimensions www.vishay.com/doc?95222						
Deut annulium information	TO-220ABPbF	www.vishay.com/doc?95225				
Part marking information	TO-220AB-N3	www.vishay.com/doc?95028				



Vishay Semiconductors

TO-220AB

DIMENSIONS in millimeters and inches



Lead assignments

Diodes

- 1. Anode/open
- 2. Cathode
- 3. Anode

Conforms to JEDEC outline TO-220AB

SYMBOL	MILLIN	MILLIMETERS		INCHES	
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

SYMBOL	MILLIM	IETERS	INCHES		NOTES
STIMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
E	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
E2	-	0.76	-	0.030	7
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6, 7
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØΡ	3.54	3.73	0.139	0.147	
Q	2.60	3.00	0.102	0.118	
θ	90° to 93°		90° t	o 93°	
		•	•	•	

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline

Lead tip



Legal Disclaimer Notice

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